

Silicon NPN Power Transistors

2N6261

DESCRIPTION

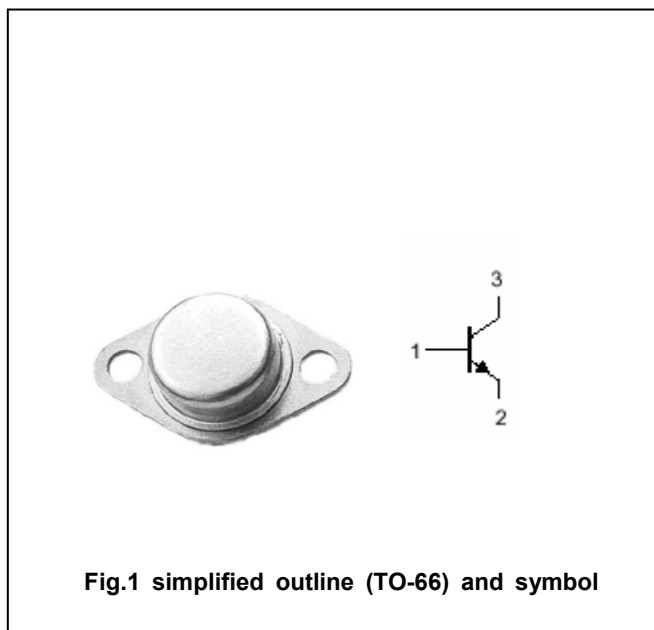
- With TO-66 package
- Low collector saturation voltage
- Wide safe operating area

APPLICATIONS

- Power switching circuits
- Series and shunt-regulator driver and output stages
- High-fidelity amplifiers
- Solenoid drivers

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	90	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		4	A
I_B	Base current		2	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	3.5	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1 A ; I _B =0	80			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.5A; I _B =0.15A			0.5	V
V _{BE}	Base -emitter on voltage	I _C =1.5A ; V _{CE} =2V			1.5	V
I _{CEV}	Collector cut-off current	V _{CE} =80V; V _{BE(off)} =-1.5V T _C =150 °C			0.5 1.0	mA
I _{CEO}	Collector cut-off current	V _{CE} =60V; I _B =0			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			0.2	mA
h _{FE-1}	DC current gain	I _C =4A ; V _{CE} =2V	5			
h _{FE-2}	DC current gain	I _C =1.5A ; V _{CE} =2V	25		100	

PACKAGE OUTLINE

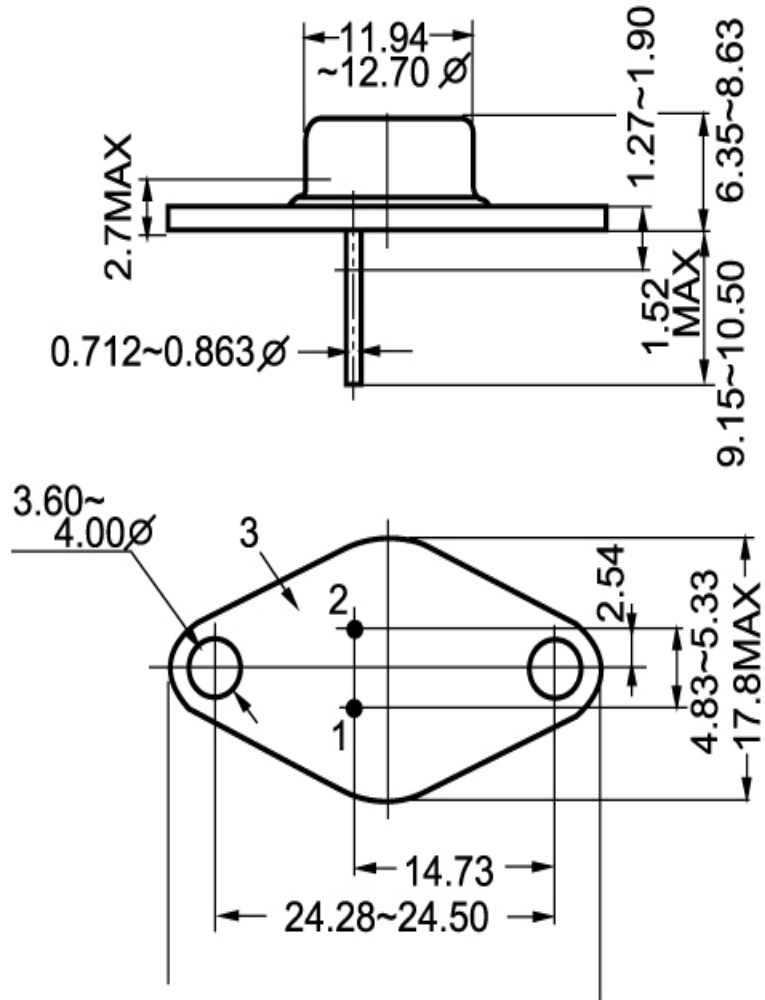


Fig.2 Outline dimensions